





P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	Package	I _D T _A = +25°C
-20V	0.9Ω @ $V_{GS} = -4.5V$	SOT23	-430mA
-20V	2.0Ω @ V _{GS} = -1.8V	30123	-150mA

Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- DC-DC Converters
- Power Management Functions

Features

- Low On-Resistance
- Very Low Gate Threshold Voltage V_{GS(TH)} <1V
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Gate
- Qualified to AEC-Q101 standards for High Reliability
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

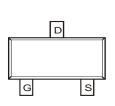
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding
 Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Terminal Connections: See Diagram
- Weight: 0.008 grams (Approximate)



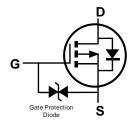


SOT23

Top View



Top View Internal Schematic



Equivalent Circuit

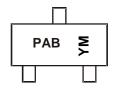
Ordering Information (Note 4)

Part Number	Compliance	Case	Packaging
DMP2004K-7	Standard	SOT23	3,000/Tape & Reel
DMP2004KQ-7	Automotive	SOT23	3,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



PAB = Product Type Marking Code YM = Date Code Marking Y = Year (ex: F = 2018) M = Month (ex: 9 = September)

Date Code Key

Year	2008		2009	~		2018	2019		2020	2021		2022
Code	V		W	~		F	G		Н			J
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	-20	V
Gate-Source Voltage	V _{GSS}	±8	V
Continuous Drain Current (Note 5) V _{GS} = -4.5V	I _D	-600	mA
Pulsed Drain Current	I _{DM}	-1.9	Α

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P _D	550	mW
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	227	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

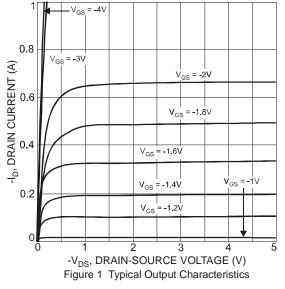
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

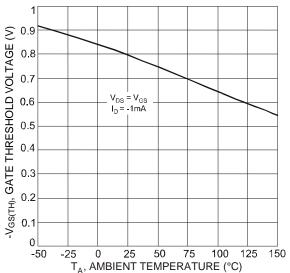
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)	•			•	•	
Drain-Source Breakdown Voltage	BV _{DSS}	-20	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-1	μΑ	V _{DS} = -20V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	_	_	±1.0	μΑ	$V_{GS} = \pm 4.5V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	V _{GS(TH)}	-0.5	1	-1.0	V	$V_{DS} = V_{GS}$, $I_D = -250\mu A$
		_	0.7	0.9	Ω	$V_{GS} = -4.5V, I_D = -430mA$
Static Drain-Source On-Resistance	R _{DS(ON)}	_	1.1	1.4		$V_{GS} = -2.5V, I_D = -300mA$
		_	1,7	2.0		$V_{GS} = -1.8V, I_D = -150mA$
Forward Transfer Admittance	Y _{fs}	200	_	_	ms	$V_{DS} = -10V, I_{D} = -0.2A$
Diode Forward Voltage (Note 6)	V _{SD}	-0.5	_	-1.2	V	V _{GS} = 0V, I _S = -115mA
DYNAMIC CHARACTERISTICS (Note 7)	•			•	•	
Input Capacitance	C _{iss}	_	_	175	pF	
Output Capacitance	Coss	_	_	30	pF	V _{DS} = -16V, V _{GS} = 0V -f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}	_	_	20	pF	1 - 1.000112
Turn-On Delay Time	t _{D(ON)}	_	8.5	_	ns	
Turn-On Rise Time	t _R	_	4.3	_	ns	$V_{DD} = -3V, V_{GS} = -2.5V,$
Turn-Off Delay Time	t _{D(OFF)}	_	20.2	_	ns	$R_L = 300\Omega, R_g = 25\Omega,$ $R_D = -100\text{mA}$
Turn-Off Fall Time	t _F		19.2	_	ns	- 100mA

Notes:

- 5. Device mounted on FR-4 PCB.
- 6. Short duration pulse test used to minimize self-heating effect.7. Guaranteed by design. Not subject to product testing.









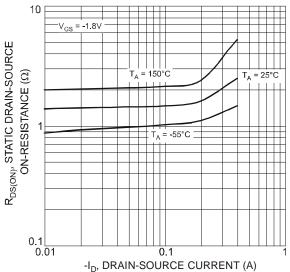


Figure 5 Static Drain-Source On-Resistance vs. Drain Current

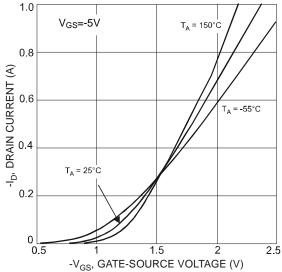


Figure 2 Typical Transfer Characteristics

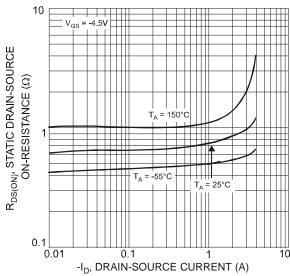


Figure 4 Static Drain-Source On-Resistance vs. Drain Current

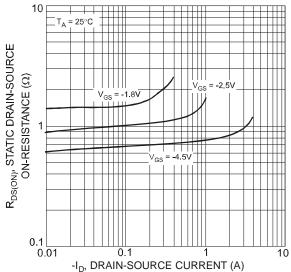


Figure 6 Static Drain-Source On-Resistance vs.
Drain-Source Current



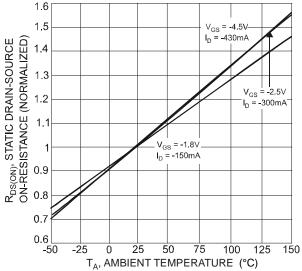


Figure 7 Static Drain-Source On-State Resistance vs. Ambient Temperature

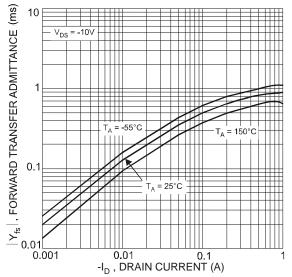


Figure 9 Forward Transfer Admittance vs. Drain Current

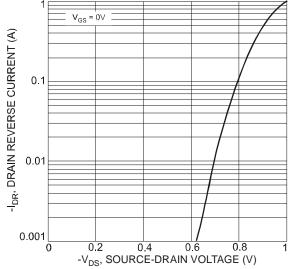
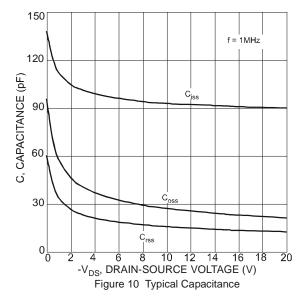


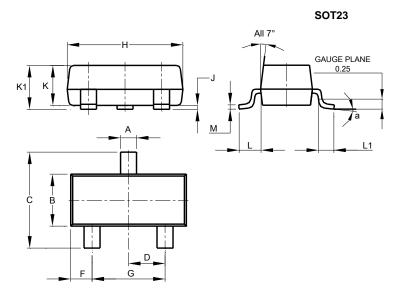
Figure 8 Reverse Drain Current vs. Source-Drain Voltage





Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

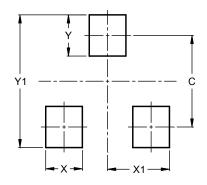


SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
U	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Η	2.80	3.00	2.90				
7	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
M	0.085	0.150	0.110				
а	0°	8°					
All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	29



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